

## High Power Amplifiers

The AHP series of high power RF amplifiers utilise GaAs FET and Silicon MOSFET technology in class A and AB linear designs to provide high RF output power over wide frequency bands with low distortion and high efficiency. These amplifiers are particularly suited to applications in RFI/EMC testing, broadcasting, communications, cellular radio, satcom, EMC, laboratory testing and TWT replacement. In addition to the standard models listed, custom units can be offered to meet the requirements of specific applications.

- 0.1 MHz – 3.0 GHz
- Wide Band
- Excellent Linearity
- Low Distortion
- High Dynamic Range
- High Efficiency
- Small Size



General Electrical Specifications	
Impedance	50 ohms
Spurious	-70dBc typ.
Output VSWR	2.0:1 typ.
Operating Environment	
Operating Case Temperature Except Models: AHP-10499-00 & AHP-10499-1-00	0 to +50C -10 to +60C
Storage Temperature	-30 +100C
Humidity	95% non-condensing

**Options:**

- 19" Rack Mounting with Forced Cooling
- Alternative RF Connectors
- Custom Frequency Ranges
- Extended Temperature Range
- Gain Control
- Reverse Polarity Protection
- Thermal Overload Protection
- Input Power Protection

Note 1: The specification is subject to regular reviews and will be updated from time to time as part of our continuing product development and improved spec accuracy.  
 Note 2: Operation beyond the quoted limits stated above may cause instantaneous and permanent damage.

